BRIDGE RECTIFIER

DB201 - DB207

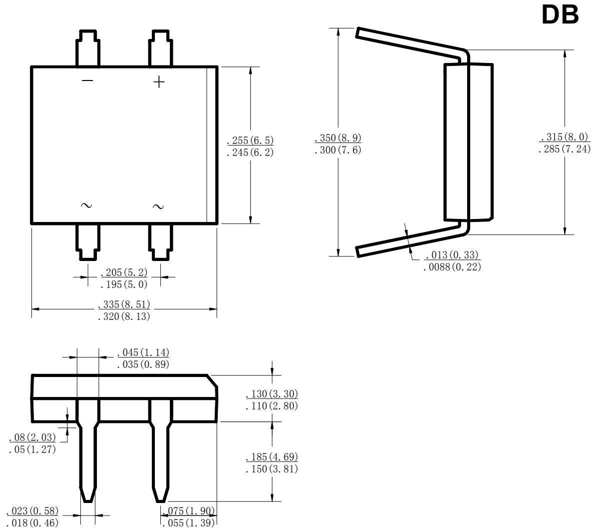
FEATURES

- Io 2A
- VRRM 50V~1000V
- Glass passivated chip
- High surge forward current capability

APPLICATIONS

- General purpose 1 phase Bridge rectifier applications

Outline Dimensions and Mark



Dimensions in inches and (millimeters)

ABSOLUTE MAXIMUM RATING

Item	Symbol	Unit	Conditions	DB2						
				01	**02**	**03**	**04**	**05**	**06**	**07**
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Average Rectified Output Current	I_O	A	60Hz ,Ta=25℃ 60Hz sine wave, R-load ,Ta=25℃	2.0						
Surge(Non-Repetitive)Forward Current	I_{FSM}	A	60H$_Z$,T$_j$=25℃60H$_Z$ sine wave, 1 cycle, T$_j$=25℃	60						
Current Squared Time	I^2t	A^2S	1ms≤t<8.3ms Tj=25℃, 1ms≤t<8.3ms Tj=25℃， Rating of per diode	15						
Storage Temperature	T_{stg}	℃		-55 ~+150						
Junction Temperature	T_j	℃		-55 ~+150						

ELECTRICAL CHARACTERISTICS (TA=25 °C)

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	I_{FM}=2.0A, I_{FM}=2.0A, Pulse measurement, Rating of per diode	1.1
Peak Reverse Current	I_{RRM}	μA	V_{RM}=V_{RRM} ,V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{θJ-A}$	℃/W	Between junction and ambient, On glass-epoxi substrate	68
	$R_{θJ-L}$		Between junction and lead	15

CHARACTERISTICS (TYPICAL)

FIG1:Io-Ta Curve

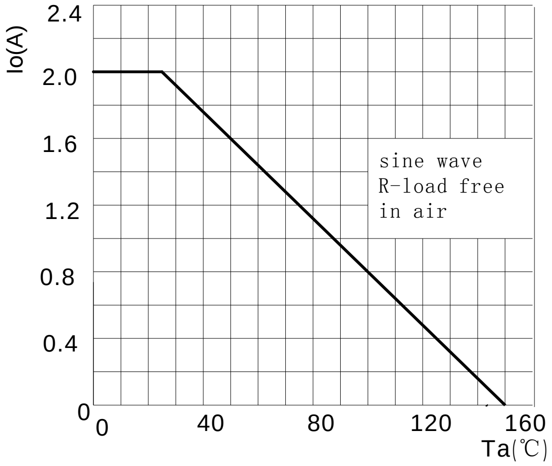


FIG2:Surge Forward Current Capability

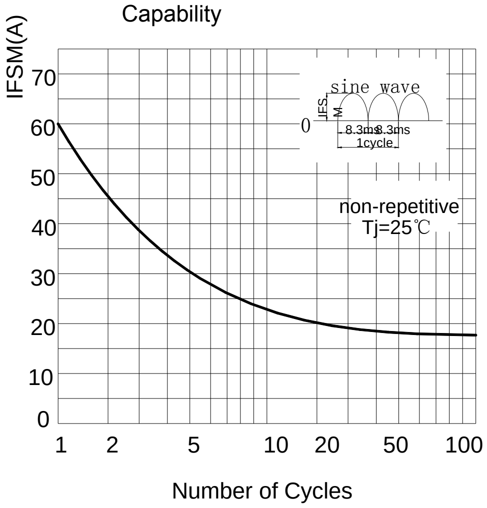


FIG3: Forward Voltage

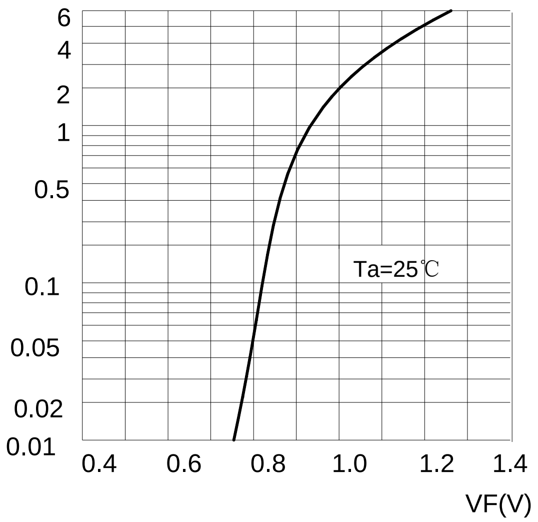


FIG4:Typical Reverse Characteristics